

## II. Outline

<b>Based spec</b>	Interface	M.2 M key
	Dimension	22*80*3.73 mm
	Weight <sup>①</sup>	<40g
	Capacity	<b>256GB, 512GB, 1TB, 2TB</b>
	Flash type	3D TLC NAND Flash
	DRAM	none
<b>Read/Write Performance</b> <sup>②</sup>	Sequential Read	Up to 2500MB/s
	Sequential Write	Up to 1860MB/s
	4KB Random Read IOPS	40K
	4KB Random Write IOPS	46K
<b>Power Consumption</b>	Power Supply	3.3V±5%
	Standby	0.3W
	4KB Random Write	5W
<b>Reliability</b>	Write endurance: 8 years @ 100G write/day(128G)	
	Read endurance: unlimited	
	MTBF: >2,000,000 hours	
	Data retention: >20years @ 25℃	
	Data destroy do not support	
	Sudden power-off recovery support	
	S.M.A.R.T,NCQ,Trim and dynamic power management support	
	Static and dynamic wear-leveling	
	Bad block management algorithm	
	ECC: LDPC ECC	
<b>Environment</b>	Storage temperature: -40~85 ℃	
	Operation temperature: Optional	
	Humidity: 5%~95%	
	Vibration: 20G Peak, 10 ~ 2000Hz, (15mins/ Axis) x3 Axis	
	Shock: 1500G (@0.5ms half sine wave)	
<b>Warranty</b>	<b>1 Year</b>	

①, ②: The Read/Write performance and weight vary with different capacity of products.

The testing environment is below:

OS: Windows 7 Ultimate

CPU: Intel (R) Core(TM) i3 CPU

Memory: 8GB                      Motherboard:B250

Test program: ATTOBenchMark V2.47 (sequential R/W speed)

IOmeter2008 (IOPS)

HD tune V4.6.1 (sustainably R/W speed, access time)

Test Drive: 07-N-M2M-PCIE-256      (3D TLC)